

## SANYO Semiconductors DATA SHEET

N-Channel Junction Silicon FET

# **25K3796**—Low-Frequency General-Purpose Amplifier, **Impedance Converter Applications**

### **Applicatins**

· Low-frequency general-purpose amplifier, impedance conversion, analog switches applications.

#### **Features**

- · Small IGSS.
- Small Ciss

#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSX</sub>		30	V
Gate-to-Drain Voltage	V <sub>GDS</sub>		-30	V
Gate Current	IG		10	mA
Drain Current	ID		10	mA
Allowable Power Dissipation	PD		100	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
	Syllibol		min	typ	max	Offic
Gate-to-Drain Breakdown Voltage	V(BR)GDS	I <sub>G</sub> =-10μA, V <sub>DS</sub> =0V	-30			V
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V			-1.0	nA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1μA	-0.18	-0.95	-2.2	V

Marking: K Continued on next page.

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#### 2SK3796

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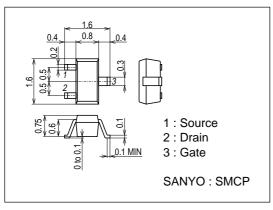
Parameter	Symbol	Conditions	Ratings			Unit
i diametei	Gymbol	Conditions	min	typ	max	Offic
Drain Current	IDSS	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V	0.6*		6.0*	mA
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1kHz	3.0	6.5		mS
Input Capacitance	Ciss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz		4		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz		1.1		pF
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)	V <sub>DS</sub> =10mV, V <sub>GS</sub> =0V		200		Ω

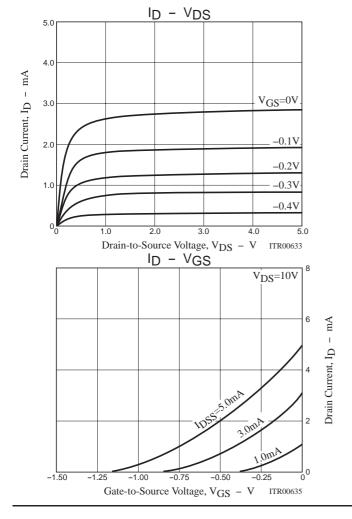
\*: The 2SK3796 is classified by IDSS as follows: (unit: mA).

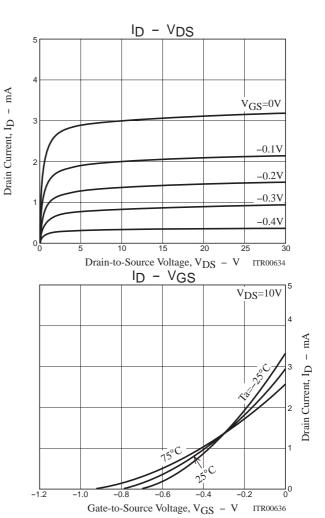
Rank	2	3	4	
IDSS	0.6 to 1.5	1.2 to 3.0	2.5 to 6.0	

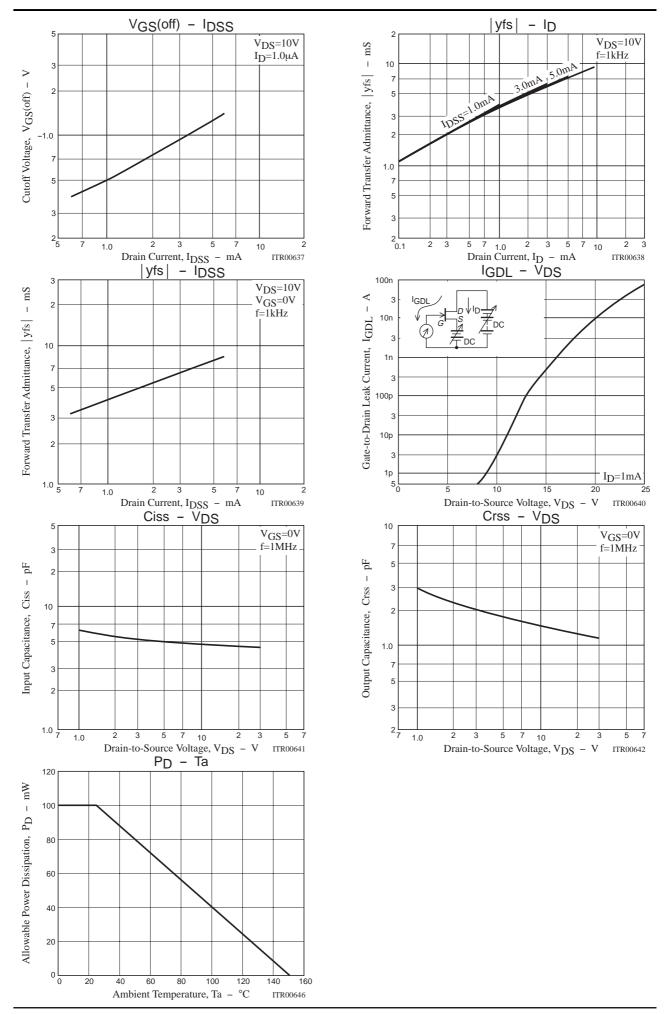
#### **Package Dimensions**

unit : mm (unit) 7027-003









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